

......

1200V, 75A, Trench FS II Fast IGBT

General Description:

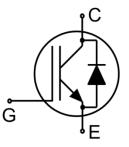
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology Offering
- Very low V_{CE(sat)}
- High speed switching
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- PV power
- Three-level Solar String Inverter



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking		
NCE75TD120VTP	TO-247P	NCE75TD120VTP		



TO-247P

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vces	Collector-Emitter Voltage	1200	V
V_{GES}	Gate- Emitter Voltage	±30	V
I-	Collector Current	150	Α
lc	Collector Current @T _C = 100 °C	75	А
I _{Cpuls}	Pulsed Collector Current, tp limited by T _{jmax}	225	А
-	turn off safe operating area, V _{CE} =1200V, Tj=150°C	225	А
l _F	Diode Continuous Forward Current @T _C = 100 °C	75	А
I _{FM}	Diode Maximum Forward Current	225	А
Ĺ	Power Dissipation @ T _C = 25°C	833	W
P _D	Power Dissipation @T _C = 100 °C	417	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	°C
T∟	Maximum Temperature for Soldering	260	°C



Thermal Characteristic

Symbol	Parameter	Value	Units
Rejc	Thermal Resistance, Junction to case for IGBT	0.18	°C/W
Rejc	Thermal Resistance, Junction to case for Diode	0.4	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (Tc=25°C unless otherwise noted)

Ol	Dament and	0	!!!		Value			
Symbol	Parameter	Cond	Conditions		Тур.	Max.	Units	
Static Chara	cteristics	•		•				
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	1200			V	
Ices	Collector-Emitter Leakage Current	V _{GE} =0V,	/ _{CE} =1200V			5	uA	
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30	V,Vce=0V			200	nA	
I _{GES(R)}	Gate to Emitter Reverse Leakage	V _{GE} =-30	V,Vce =0V			200	nA	
V	Collector Fraitter Cottonation Voltage	Ic=75A	Tj=25°C		1.85	2.05	V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V	Tj=150°C		2.05		V	
$V_{\text{GE(th)}}$	Gate Threshold Voltage	Ic=1mA	,Vce=Vge	4.5		6.5	V	
Dynamic Ch	aracteristics							
Cies	Input Capacitance	V 20V	/		9747			
Coes	Output Capacitance		/,V _{GE} =0V,		327		pF	
Cres	Reverse Transfer Capacitance]	f=1MHz		271			
Qg	Total Gate Charge				572		nC	
Q _{ge}	Gate to Emitter Charge	Vcc=960V, Ic=75A, V _{GE} =15V			69			
Q_{gc}	Gate to Collector Charge		_ VGE=13V		368			
Switching Cl	haracteristics							
t _{d(ON)}	Turn-on Delay Time				19			
t _r	Rise Time				17		ne	
t _{d(OFF)}	Turn-Off Delay Time	Vce=600	V,I _C =75A,		170		ns	
t _f	Fall Time	V _{GE} =0/1	5V, R _g =8Ω		18			
Eon	Turn-On Switching Loss	Inducti	ve Load		5.6			
E _{off}	Turn-Off Switching Loss				2.7		mJ	
Ets	Total Switching Loss		1		8.3			

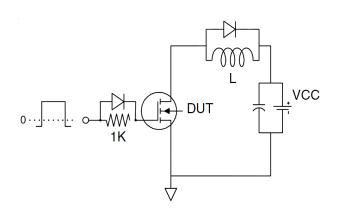
Electrical Characteristics of the Diode (T_C= 25°C unless otherwise specified)

Symbol	Doromotor	Canditions	Rating			Units	
Symbol	Parameter	Conditions	Min.	Тур.	Max.	X.	
V _{FM}	Diode Forward Voltage	I _F =75A		2.2	3.0	V	
Trr	Reverse Recovery Time	1 27.54		180		ns	
I _{RRM}	Diode Peak Reverse Recovery Current	I⊧=37.5A, di/dt=800A/us		29		А	
Qrr	Reverse Recovery Charge	ai/at=600A/us		4.3		uC	
Pulse width t _t	Pulse width $t_p \le 380 \mu s, \delta \le 2\%$						

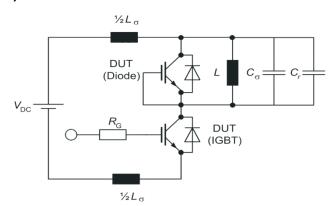


Test Circuit

1) Gate Charge Test Circuit

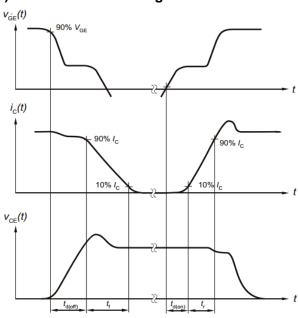


2) Switch Time Test Circuit

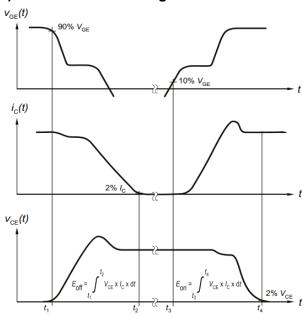


Switching characteristics

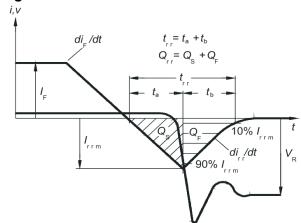
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics





Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

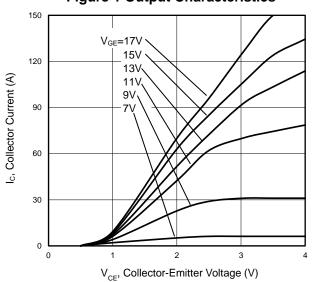


Figure 3 V_{CE(sat)} vs. Case Temperature

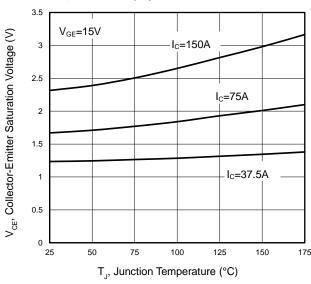


Figure 5 Capacitance Characteristics

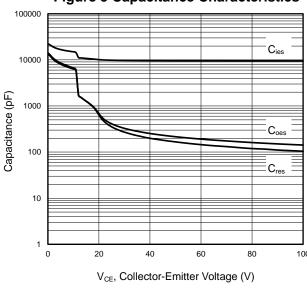


Figure 2 Transfer Characteristics

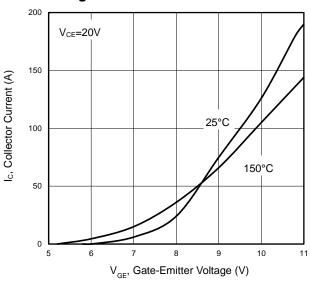


Figure 4 Saturation Voltage vs. V_{GE}

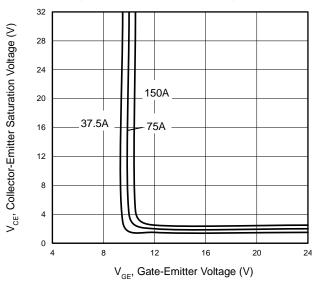
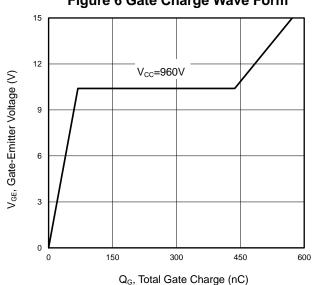
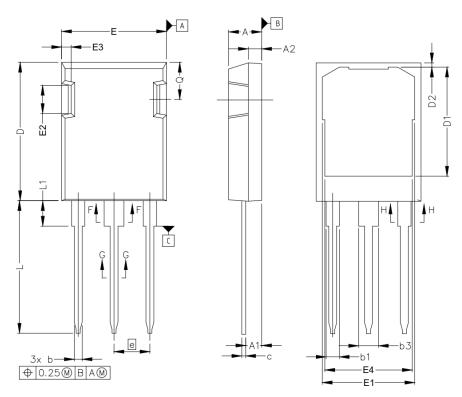


Figure 6 Gate Charge Wave Form





TO-247P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.83	5.21	0.19	0.21	
A1	2.29	2.54	0.09	0.10	
A2	1.91	2.16	0.08	0.09	
b	1.07	1.33	0.04	0.05	
b1	1.91	2.41	0.08	0.09	
b3	2.87	3.38	0.11	0.13	
С	0.55	0.68	0.02	0.03	
D	20.80	21.10	0.82	0.83	
D1	16.25	17.65	0.64	0.69	
D2	0.50	0.80	0.02	0.03	
E	15.75	16.13	0.62	0.64	
E1	13.10	14.15	0.52	0.56	
E2	3.68	5.10	0.14	0.20	
E3	1.00	1.90	0.04	0.07	
E4	12.38	13.43	0.49	0.53	
е	5.44	BSC	0.2	0.21	
N	3.	00	0.12		
L	19.81	20.32	0.78	0.80	
L1	3.70	4.00	0.15	0.16	
Q	5.49	6.00	0.22	0.24	





NCE75TD120VTP

Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.

单击下面可查看定价,库存,交付和生命周期等信息

>>NCEPOWER(无锡新洁能)